

Features

- Input Voltage up to 24V
- MOSFET Turn on Resistor RSS(ON)
=35mohm(Max)@Vgs=4.5V
- Drain to Drain MOSFET Module
- With ESD Protection
- Continuous Current=5A
- Green Product (RoHS, Lead-Free, Halogen-Free Compliant)

General Description

The GS95A9CS-R drain to drain connected MOSFET module provides an integrated solution with small dimension for battery pack of Mobile phone and electronic bracelet application.

Applications

- Mobile phone
- Electronic Bracelet

Typical Application

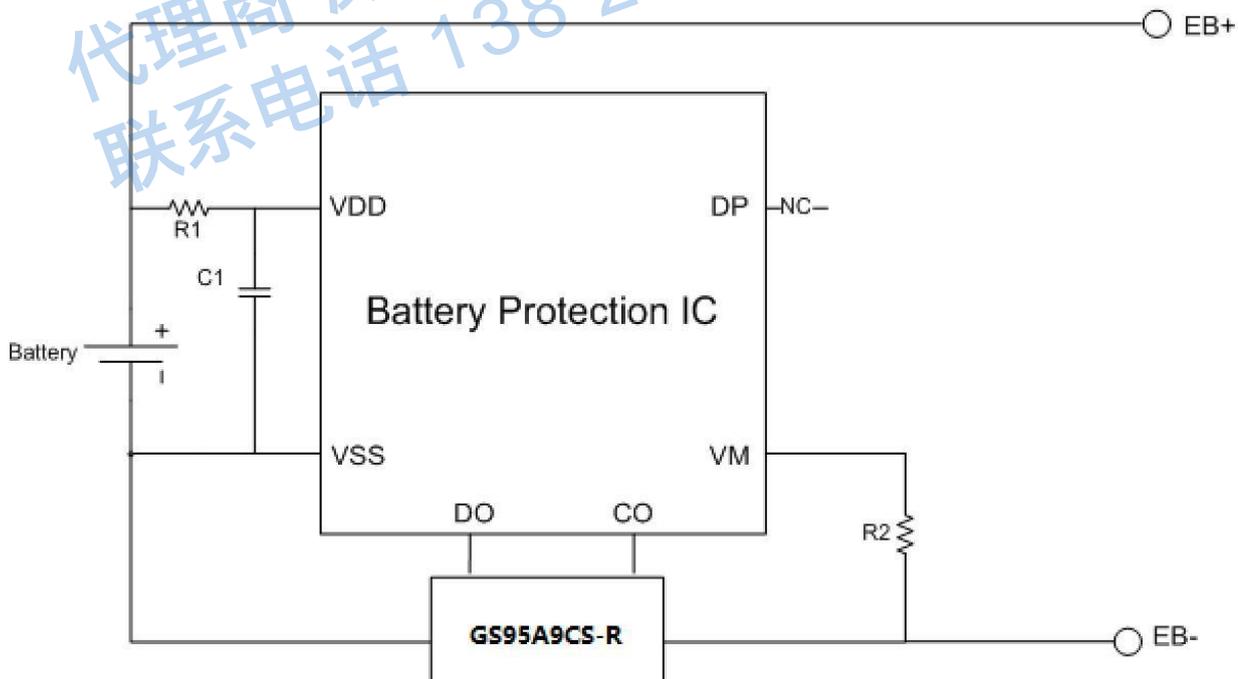


Figure 1 Application of GS95A9CS-R used in battery pack

Function Block Diagram

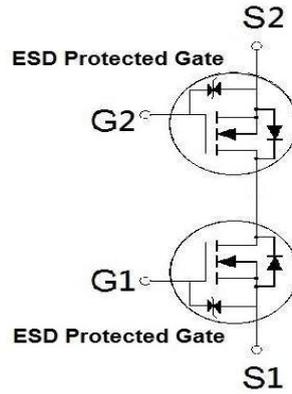


Figure 2 Function Block Diagram

Pin Configuration

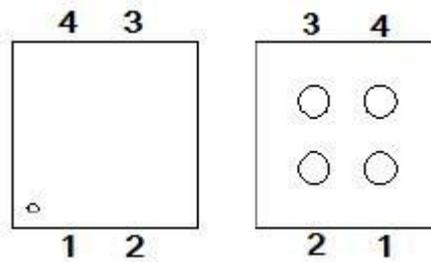


Figure 3 WLCSP 1.1 x 1.1

Pin Descriptions

| No. | Name | I/O type | Description |
|-----|------|----------|-------------|
| 1 | S1 | I/O | Source1 |
| 2 | G1 | I | Gate1 |
| 3 | G2 | I | Gate2 |
| 4 | S2 | I/O | Source2 |

Absolute Maximum Ratings (T_A=25°C Unless Otherwise Noted)

| PARAMETER / TEST CONDITIONS | SYMBOL | LIMITS | UNITS |
|------------------------------------------------|-----------------------------------|---------|-------|
| Source-Source Voltage | V _{SSS} | 24 | V |
| Gate-Source Voltage | V _{GSS} | ±12 | V |
| Continuous Source Current | I _S | 5 | A |
| Pulsed Source Current ¹ | I _{SP} | 50 | A |
| Total Dissipation ² | P _T | 1.6 | W |
| Thermal Resistance ² | R _{θJA} | 60 | °C/W |
| Operating Junction & Storage Temperature Range | T _J & T _{stg} | -55~150 | °C |

¹PW≤10μs, duty cycle≤1%.

²When mounted on 1in² FR-4 board.

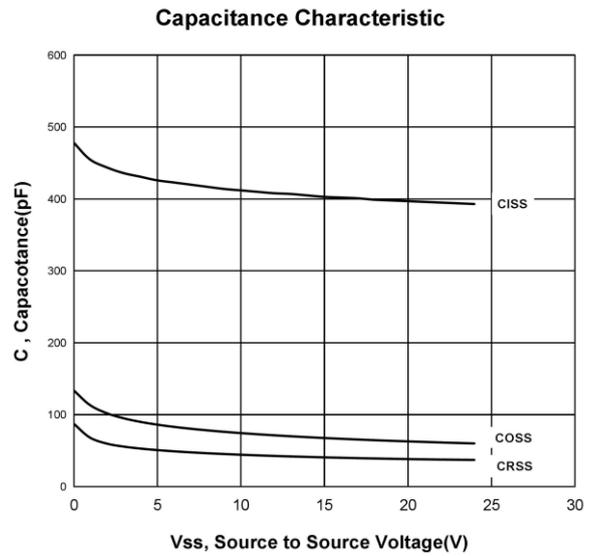
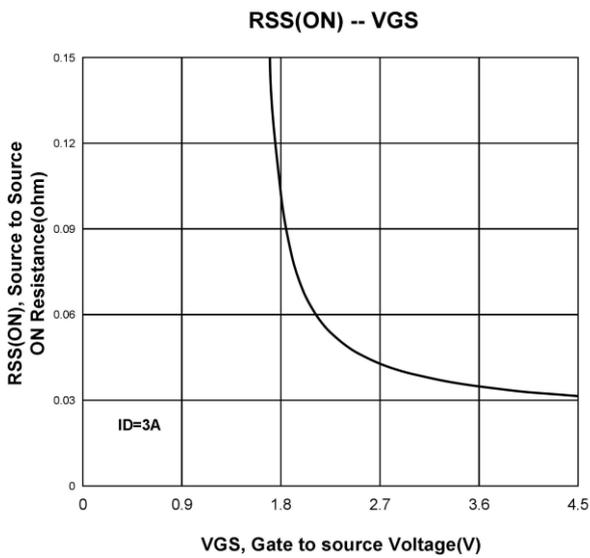
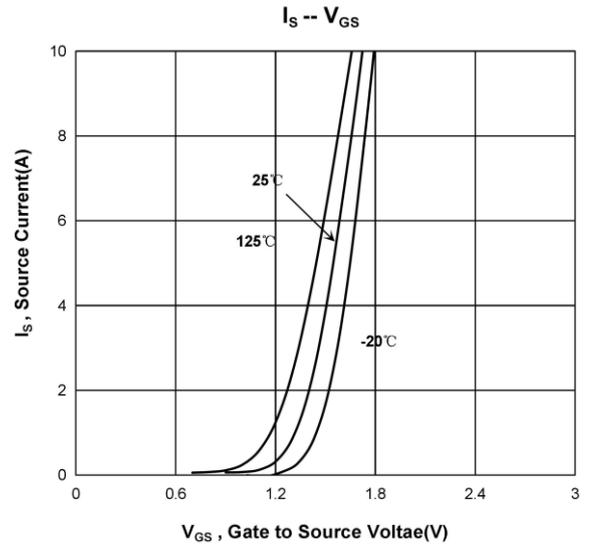
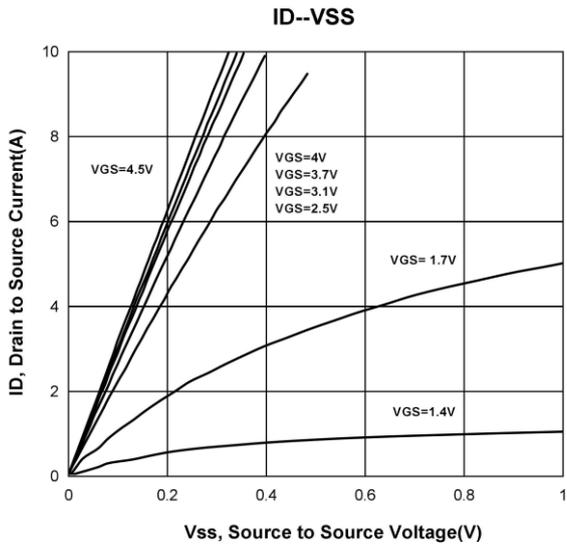
Electrical Characteristics (T_J=25°C Unless Otherwise Noted)

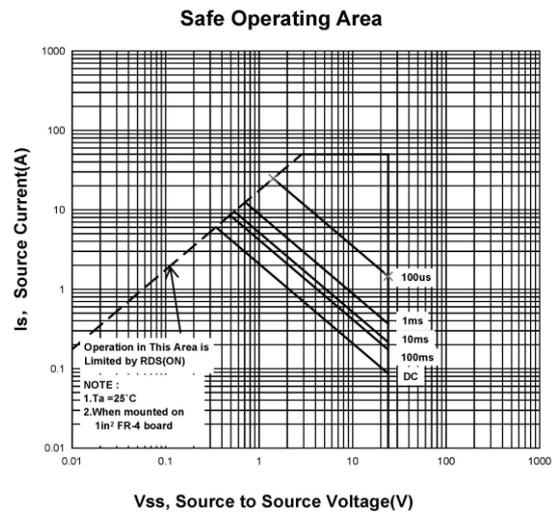
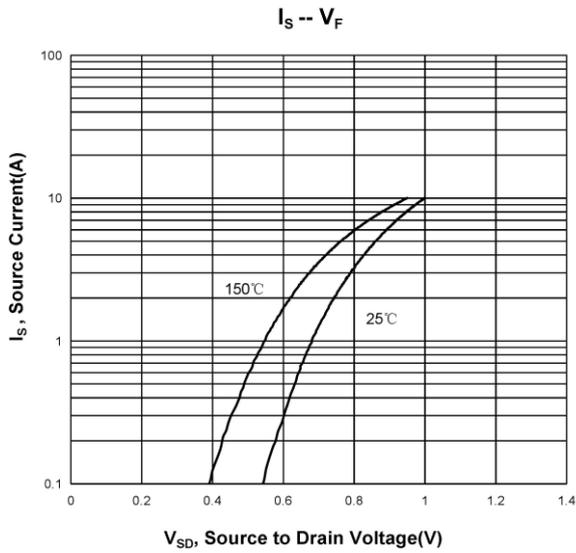
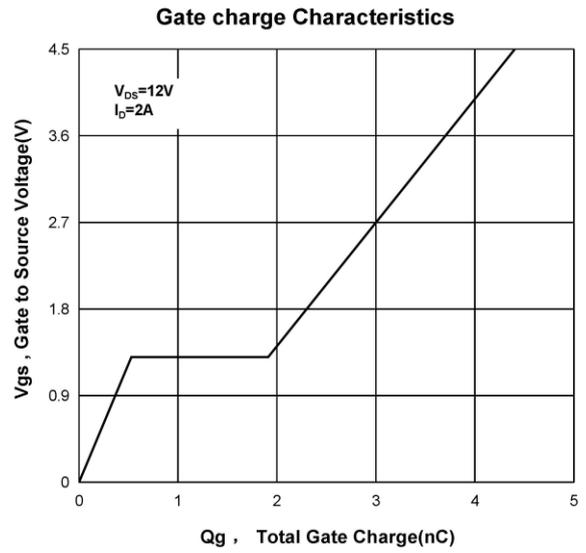
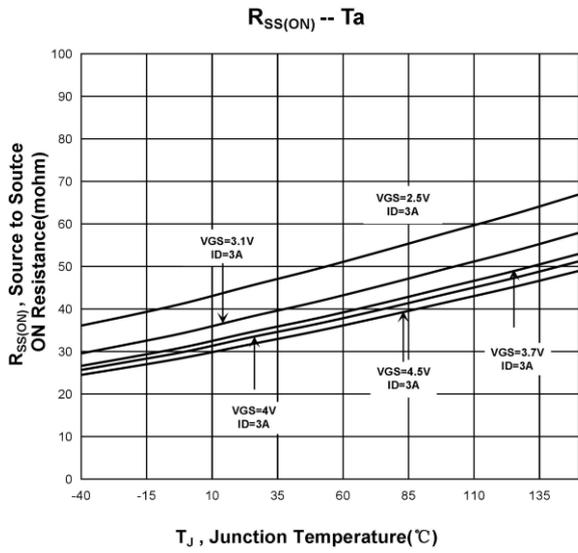
| PARAMETER | SYMBOL | TEST CONDITIONS | LIMITS | | | UNITS |
|-------------------------------------------------|----------------------|-------------------------------------------------------|--------|-----|-----|-------|
| | | | MIN | TYP | MAX | |
| STATIC | | | | | | |
| Source-Source Breakdown Voltage | V _{(BR)SSS} | V _{GS} = 0V, I _S = 1mA | 24 | | | V |
| Gate Threshold Voltage | V _{GS(th)} | V _{SS} = 10V, I _S = 1mA | 0.7 | 1.1 | 1.5 | |
| Gate-Source Leakage | I _{GSS} | V _{SS} = 0V, V _{GS} = ±8V | | | ±10 | uA |
| | | V _{SS} = 0V, V _{GS} = ±5V | | | ±2 | |
| Zero Gate Voltage Source Current | I _{SSS} | V _{SS} = 20V, V _{GS} = 0V | | | 1 | uA |
| Source -Source On-State Resistance ¹ | R _{SS(ON)} | V _{GS} = 4.5V, I _S = 3A | 26 | 32 | 35 | mΩ |
| | | V _{GS} = 4V, I _S = 3A | 27 | 34 | 41 | |
| | | V _{GS} = 3.7V, I _S = 3A | 28 | 35 | 42 | |
| | | V _{GS} = 3.1V, I _S = 3A | 30 | 40 | 48 | |
| | | V _{GS} = 2.5V, I _S = 3A | 36 | 50 | 58 | |
| Forward Transconductance ¹ | g _{fs} | V _{SS} = 5V, I _S = 3A | | 19 | | S |
| DYNAMIC | | | | | | |
| Input Capacitance | C _{iss} | | | 440 | | pF |
| Output Capacitance | C _{oss} | V _{GS} = 0V, V _{DS} = 12V, f = 1MHz | | 80 | | |

| | | | | | | |
|---------------------------------------------------------------------------------------|--------------|---------------------------------------------|--|------|-----|----|
| Reverse Transfer Capacitance | C_{rSS} | | | 55 | | |
| Total Gate Charge ² | Q_g | $V_{SS} = 12V, V_{GS} = 4.5V, I_S = 2A$ | | 4.8 | | nC |
| Turn-On Delay Time ² | $t_{d(on)}$ | $V_{SS} = 12V, I_S \cong 2A, V_{GS} = 4.5V$ | | 13 | | nS |
| Rise Time ² | t_r | | | 39 | | |
| Turn-Off Delay Time ² | $t_{d(off)}$ | | | 24 | | |
| Fall Time ² | t_f | | | 47 | | |
| SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^\circ C$) | | | | | | |
| Forward Source-Source Voltage ¹ | V_F | $I_S = 2A, V_{GS} = 0V$ | | 0.77 | 1.2 | V |

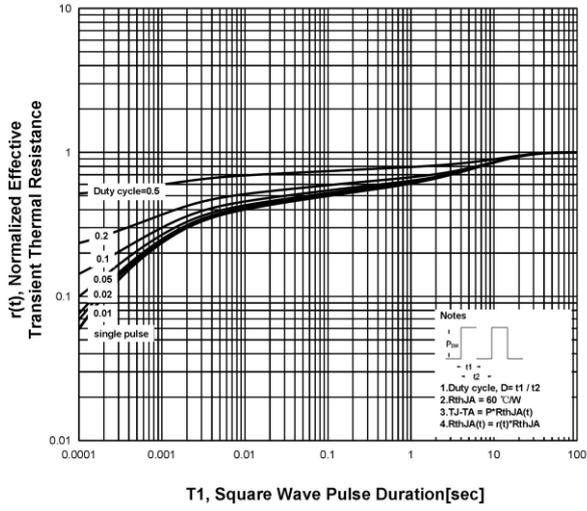
¹Pulse test : Pulse Width $\leq 300 \mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

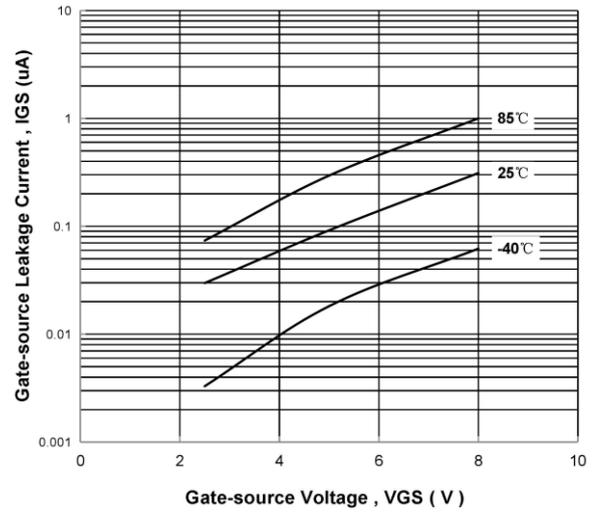




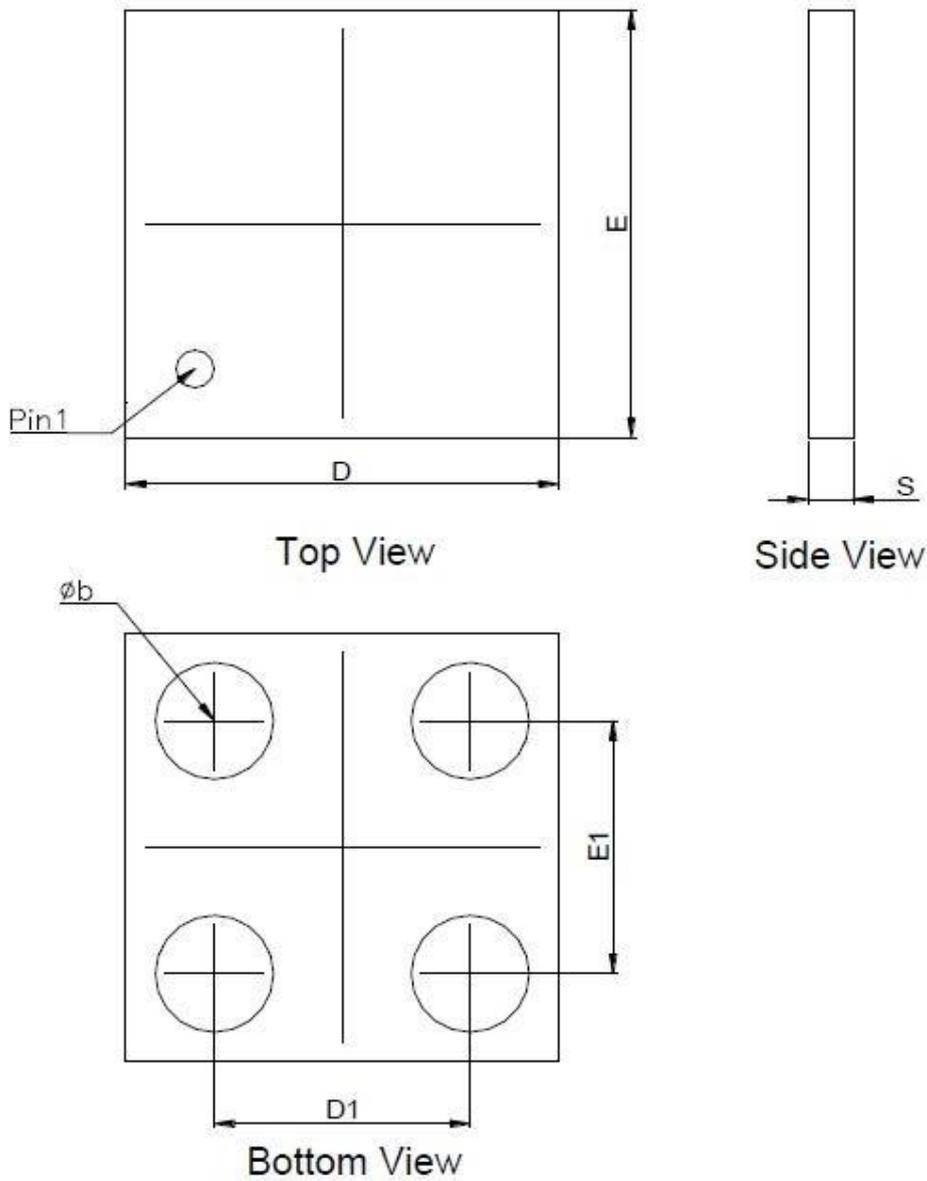
Transient Thermal Response Curve



IGS - VGS



Package Dimensions, WLCSP 1.1x1.1

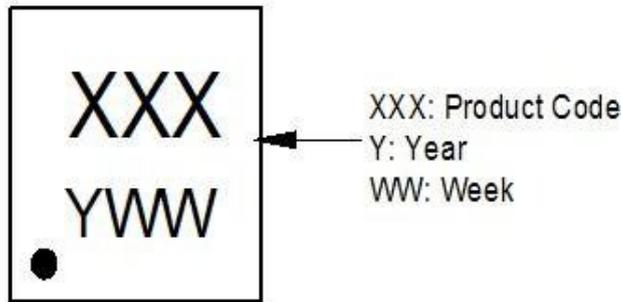


| Symbol | Dimensions in Millimeters | | |
|----------|---------------------------|-------|-------|
| | Min. | Typ. | Max. |
| ϕb | | 0.3 | |
| D | 1.05 | 1.1 | 1.15 |
| $D1$ | | 0.65 | |
| E | 1.05 | 1.1 | 1.15 |
| $E1$ | | 0.65 | |
| S | 0.095 | 0.115 | 0.135 |

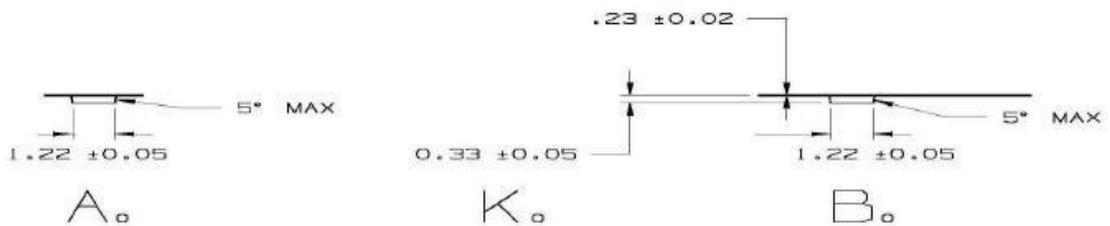
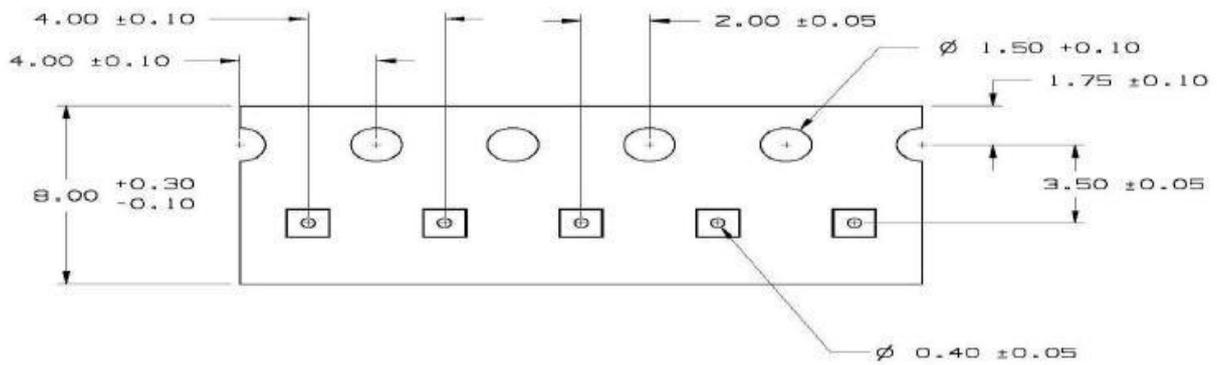
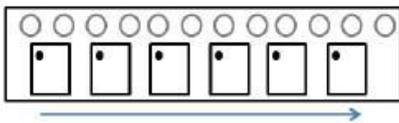
Note

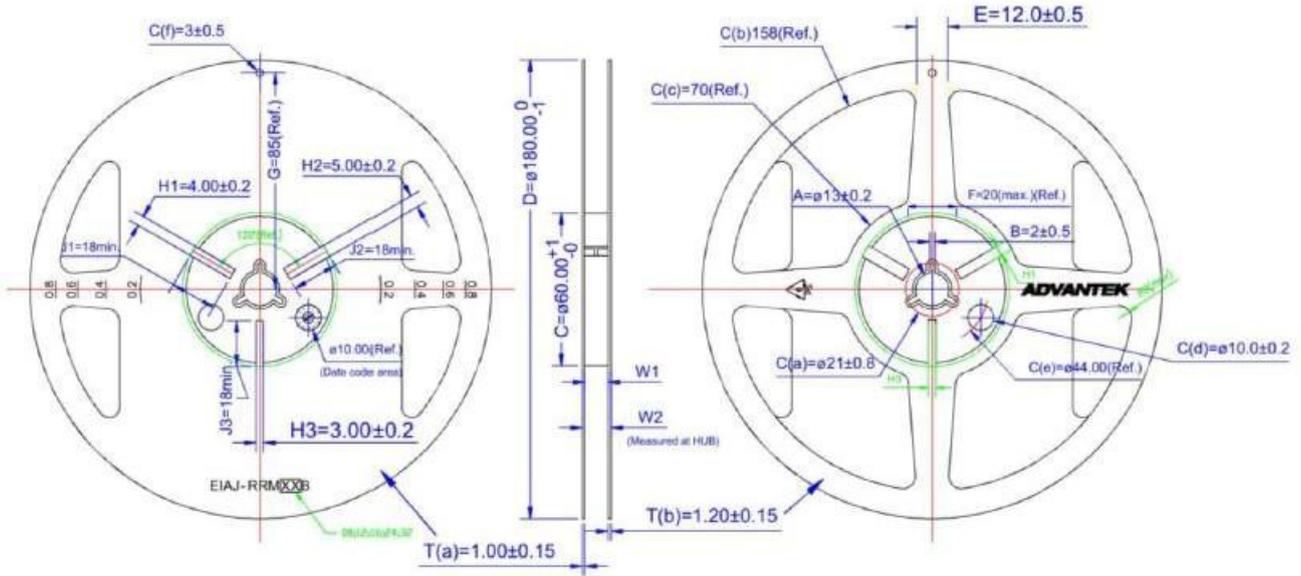
- 1.Min.: Minimum dimension specified.
- 2.Max.: Maximum dimension specified.
- 3.Typ.: Type. Typical dimension specified for reference.

A. Marking Information(Product Code: A22)



B. Tape&Reel Information:5000pcs/Reel

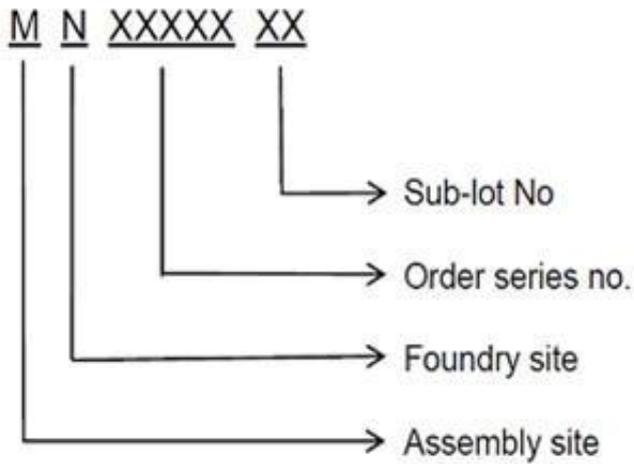




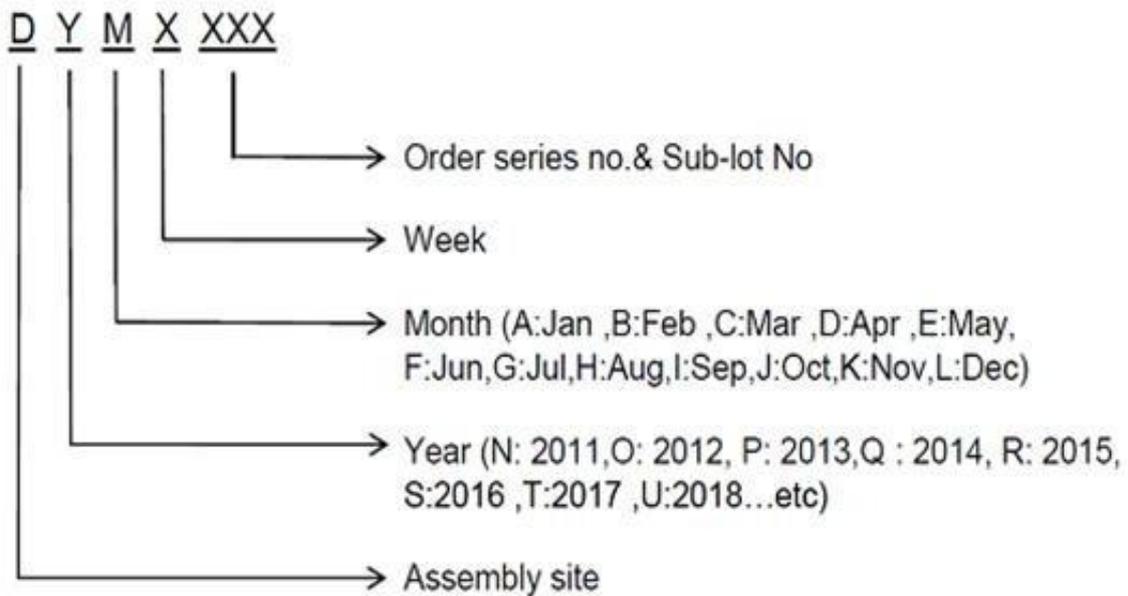
Note: All Dimension in millimeter

C. Lot No. & Date Code Rule

1. Lot No.



2. Date Code



D.Label rule

Label content



| | | |
|----|--------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| 1 | Label Size | 30 * 90 mm |
| 2 | Font style | Times New Roman or Arial (或可区分英文"0"和数字"0", "G"和"Q"的字型即可) |
| 3 | U-NIKC | Height: 4 mm |
| 4 | Package | Height: 2 mm |
| 5 | Date | Height: 2 mm Shipping date: YYYY/MM/DD, ex. 2008/09/12 |
| 6 | Device | Height: 3 mm (Max: 16 Digit) |
| 7 | Lot | Height: 3 mm (Max: 9 Digit) Sub lot |
| 8 | D/C | Height: 3 mm (Max: 7 Digit) |
| 9 | QTY | Height: 3 mm (Max: 6 Digit) Thousand mark is no needed |
| 10 | RoHS label |  long axis: 12 mm minor axis:6 mm bottom color: White Font color: Black Font style: Arial |
| 11 | Halogen Free label |  Diameter: 10 mm bottom color: Green Font color: Black Font style: Arial |
| 12 | Scan information | Device / Lot / D/C / QTY , Insert " / " between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least |

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